NPN General Purpose Transistor

The NST3904F3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE}, 100-300
- Low $V_{CE(sat)}$, $\leq 0.4 \text{ V}$
- Reduces Board Space
- This is a Pb-Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	40	Vdc
Collector - Base Voltage	V_{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	I _C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 1)	290 2.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	432	°C/W
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 2)	347 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	360	°C/W
Thermal Resistance, Junction-to-Lead 3	R _{ΨJL} (Note 2)	143	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C

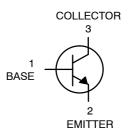
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. 100 mm² 1 oz, copper traces.
- 2. 500 mm² 1 oz, copper traces.



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NST3904F3T5G



SOT-1123 CASE 524AA STYLE 1

MARKING DIAGRAM



2 = Device CodeM = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NST3904F3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}\text{C unless otherwise noted})$

C	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS		1		•	· I
Collector - Emitter Breakdown Volta	V _{(BR)CEO}	40	-	Vdc	
Collector - Base Breakdown Voltag	ge ($I_C = 10 \mu Adc, I_E = 0$)	V _{(BR)CBO}	60	-	Vdc
Emitter - Base Breakdown Voltage	V _{(BR)EBO}	6.0	-	Vdc	
Collector Cutoff Current (V _{CE} = 30	ctor Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)			50	nAdc
ON CHARACTERISTICS (Note 3)		•	•	•	•
DC Current Gain $ \begin{aligned} &(I_C = 0.1 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ &(I_C = 1.0 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ &(I_C = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ &(I_C = 50 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ &(I_C = 100 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \end{aligned} $		h _{FE}	40 70 100 60 30	- 300 - -	-
	V _{CE(sat)}	- -	0.2 0.3	Vdc	
$\begin{aligned} \text{Base-Emitter Saturation Voltage} \\ & \text{(I}_{\text{C}} = 10 \text{ mAdc, I}_{\text{B}} = 1.0 \text{ mAdc)} \\ & \text{(I}_{\text{C}} = 50 \text{ mAdc, I}_{\text{B}} = 5.0 \text{ mAdc)} \end{aligned}$	V _{BE(sat)}	0.65 -	0.85 1.0	Vdc	
SMALL-SIGNAL CHARACTERIS	TICS				•
Current - Gain - Bandwidth Produc	ct (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	200	_	MHz
Output Capacitance (V _{CB} = 5.0 Vd	C _{obo}	-	4.0	pF	
Input Capacitance (V _{EB} = 0.5 Vdc,	C _{ibo}	-	8.0	pF	
Noise Figure (V _{CE} = 5.0 Vdc, I _C =	NF	-	5.0	dB	
SWITCHING CHARACTERISTICS	3			_	
Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc})$	t _d	_	35	
Rise Time	(I _C = 10 mAdc, I _{B1} = 1.0 mAdc)	t _r	_	35	ns
Storage Time	(V _{CC} = 3.0 Vdc, I _C = 10 mAdc)	t _s – 275		275	
Fall Time	(I _{B1} = I _{B2} = 1.0 mAdc)	t _f	_	50	ns

^{3.} Pulse Test: Pulse Width \leq 300 μ s; Duty Cycle \leq 2.0%.

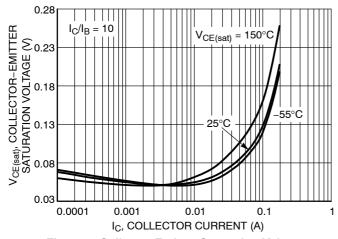


Figure 1. Collector Emitter Saturation Voltage vs.
Collector Current

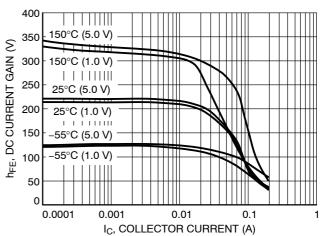


Figure 2. DC Current Gain vs. Collector Current

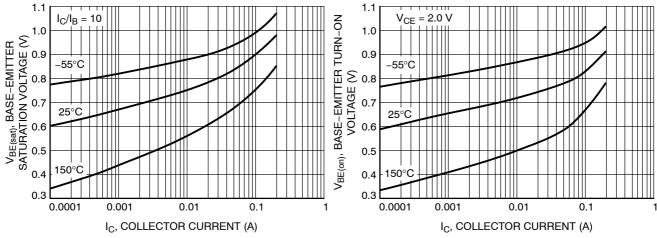


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

Figure 4. Base Emitter Turn-On Voltage vs.
Collector Current

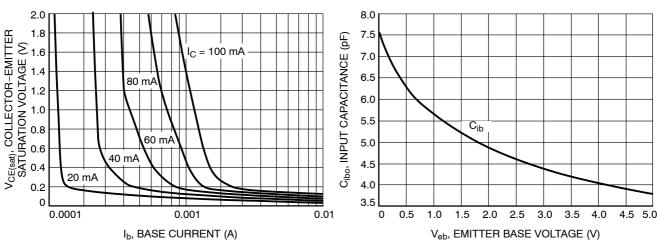


Figure 5. Saturation Region

Figure 6. Input Capacitance

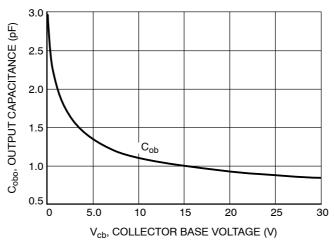
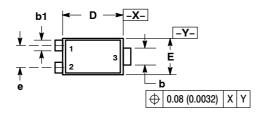
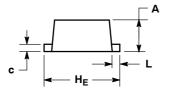


Figure 7. Output Capacitance

PACKAGE DIMENSIONS

SOT-1123 CASE 524AA-01 ISSUE A





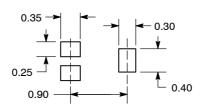
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14 FM 1092
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.34	0.37	0.40	0.013	0.015	0.016
b	0.15	0.20	0.25	0.006	0.008	0.010
b1	0.10	0.15	0.20	0.004	0.006	0.008
С	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
Е	0.55	0.60	0.65	0.022	0.024	0.026
е		0.35			0.014	
HE	0.95	1.00	1.05	0.037	0.039	0.041
Г	0.05	0.10	0.15	0.002	0.004	0.006

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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